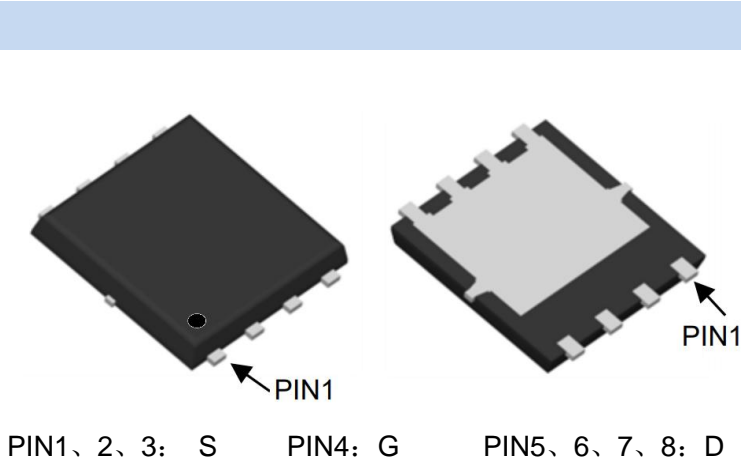
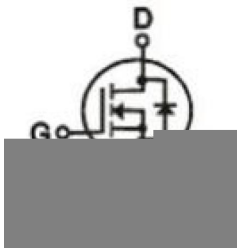


PDFN5\*6 N  
 N-Channel MOSFET in a PDFN5\*6 Plastic Package .

Low  $R_{DS(ON)}$  to minimize conductive loss;low Gate Charge for fast switching;Low Thermal resistance,  
 HF Product.

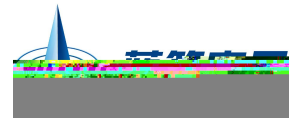
### LED

For boost converters and synchronous rectifiers for consumer, telecom, industrial power supplies and LED backlighting.



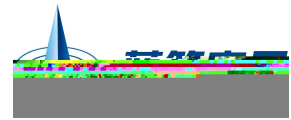
Pin	极性
1	S
2	S
3	S
4	G
5	D
6	D
7	D
8	D

见印章说明。 See Marking Instructions.

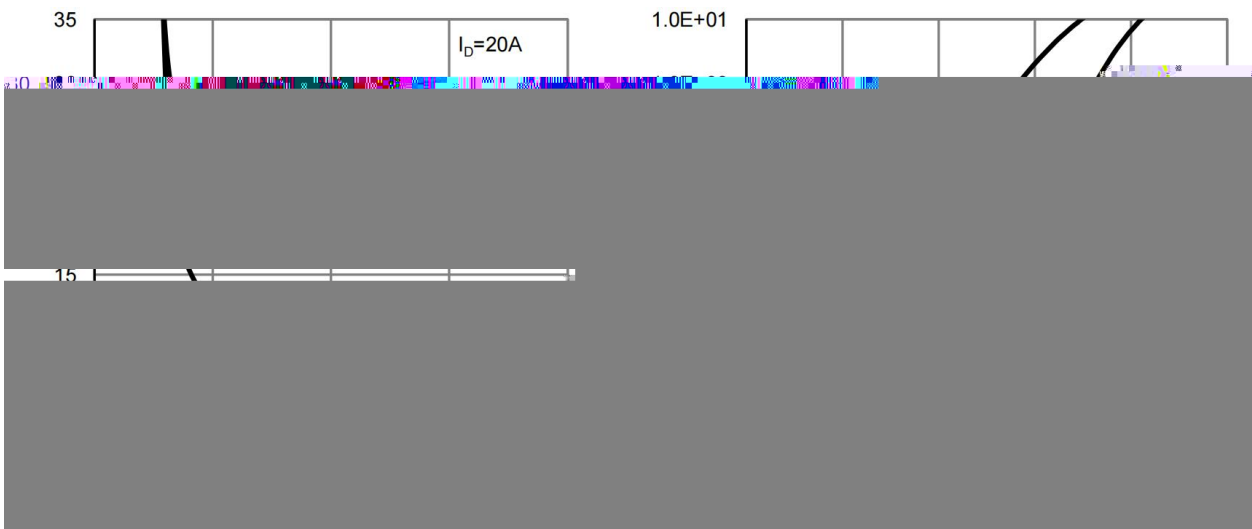
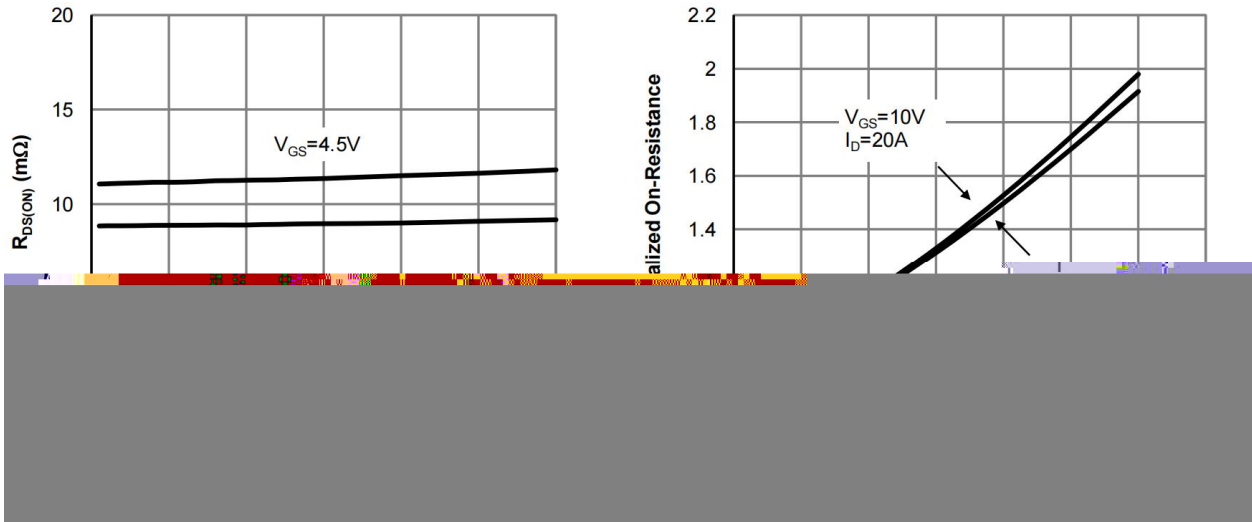
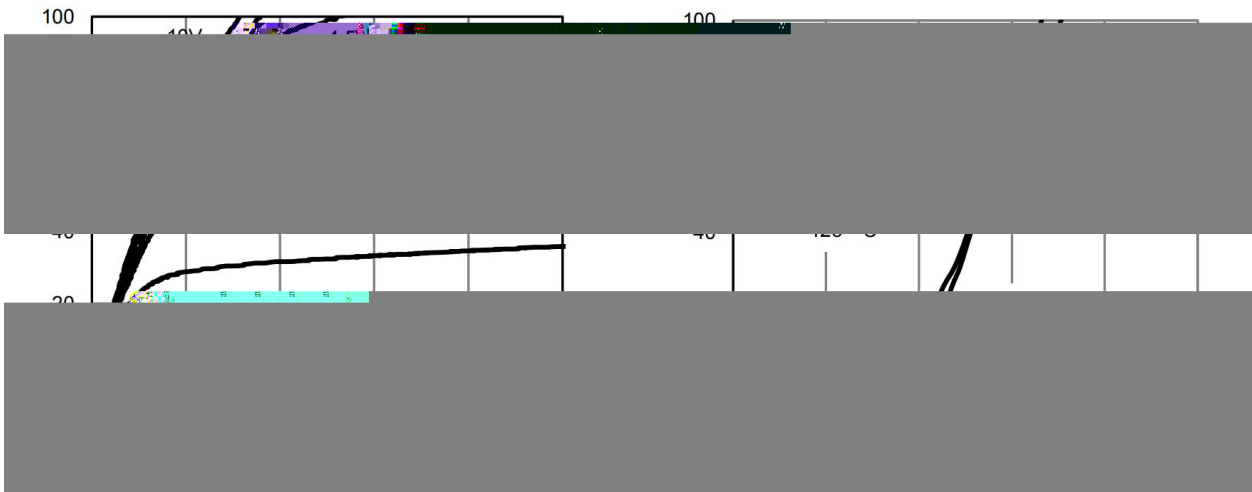
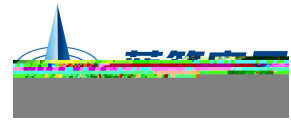


Parameter	Symbol	Rating	Unit	
Drain-Source Voltage	$V_{DS}$	100	V	
Drain Current - Continuous	$I_D$	47	A	
Drain Current – Pulsed	$I_{DM}$	105	A	
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V	
Power Dissipation	$P_D(T_c=25^\circ\text{C})$	48	W	
Single Pulse Avalanche Energy(L=0.5mH)	$E_{AS}$	78.7	mJ	
Avalanche Current(L=0.5mH)	$I_{AS}$	15	A	
Junction and Storage Temperature Range	$T_j, T_{stg}$	-55 to 150	$^\circ\text{C}$	
Thermal resistance, junction - ambient	$t \leq 10\text{s}$	$R_{JA}$	25	$^\circ\text{C/W}$
	Steady-State		55	
Thermal resistance, junction - case	Steady-State	$R_{JC}$	2.6	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$BV_{DSS}$	$I_D=250\mu\text{A}, V_{GS}=0\text{V}$	100			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=100\text{V}, V_{GS}=0\text{V}$			1.0	$\mu\text{A}$
Gate-Body leakage current	$I_{GSS}$	$V_{DS}=0\text{V}, V_{GS}=\pm 20\text{V}$			$\pm 100$	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	1.2	1.9	2.5	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=10\text{V}, I_D=20\text{A}$		8.3	12	$\text{m}\Omega$
	$R_{DS(ON)}$	$V_{GS}=4.5\text{V}, I_D=10\text{A}$		11.5	15	$\text{m}\Omega$
Drain-Source Diode Forward Voltage	$V_{SD}$	$V_{GS}=0\text{V}, I_S=1\text{A}$		0.67	1.2	V



Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Input Capacitance	$C_{iss}$	$V_{DS}=25V$ $V_{GS}=0V$ $f=1.0MHz$		2200		pF
Output Capacitance	$C_{oss}$			950		
Reverse Transfer Capacitance	$C_{rss}$			110		
Gate resistance	$R_g$	$V_{GS}=0V$ $V_{DS}=0V$ $f=1MHz$		3.3		
Total Gate Charge	$Q_{g(10V)}$	$V_{GS}=10V,$ $V_{DS}=50V$ $I_D=20A$		25		nC
Total Gate Charge	$Q_{g(4.5V)}$			12.5		
Gate Source Charge	$Q_{gs}$			6		
Gate Drain Charge	$Q_{gd}$			3.5		
Turn-On Delay Time	$t_{D(on)}$	$V_{GS}=10V, V_{DS}=50V,$ $R_L=2.5$ , $R_{GEN}=3$		8.5		ns
Turn-On Rise Time	$t_r$			3		
Turn-Off Delay Time	$t_{D(off)}$			23		
Turn-Off Fall Time	$t_f$			3.5		



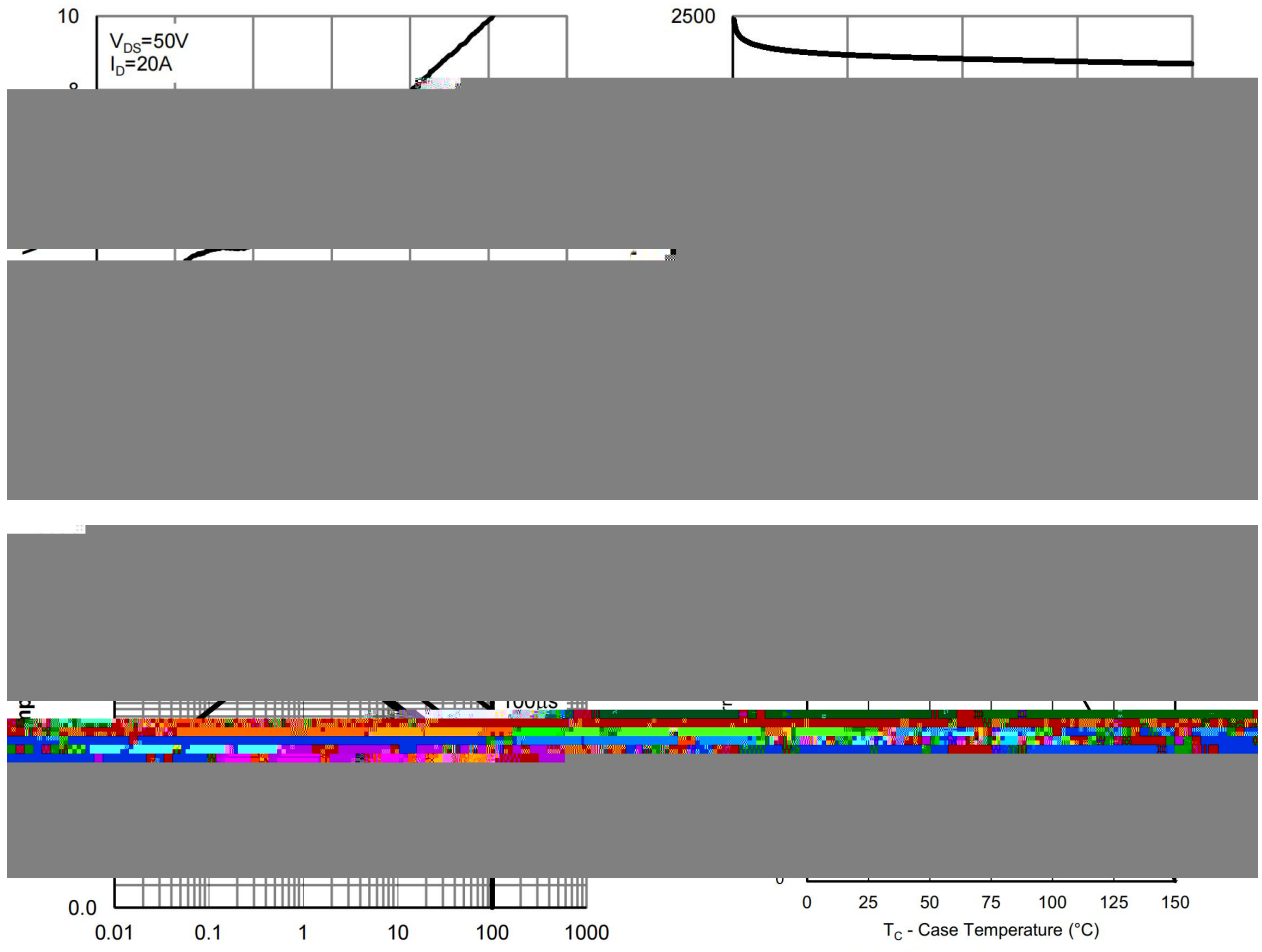
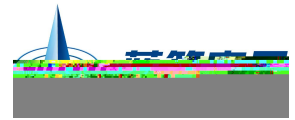
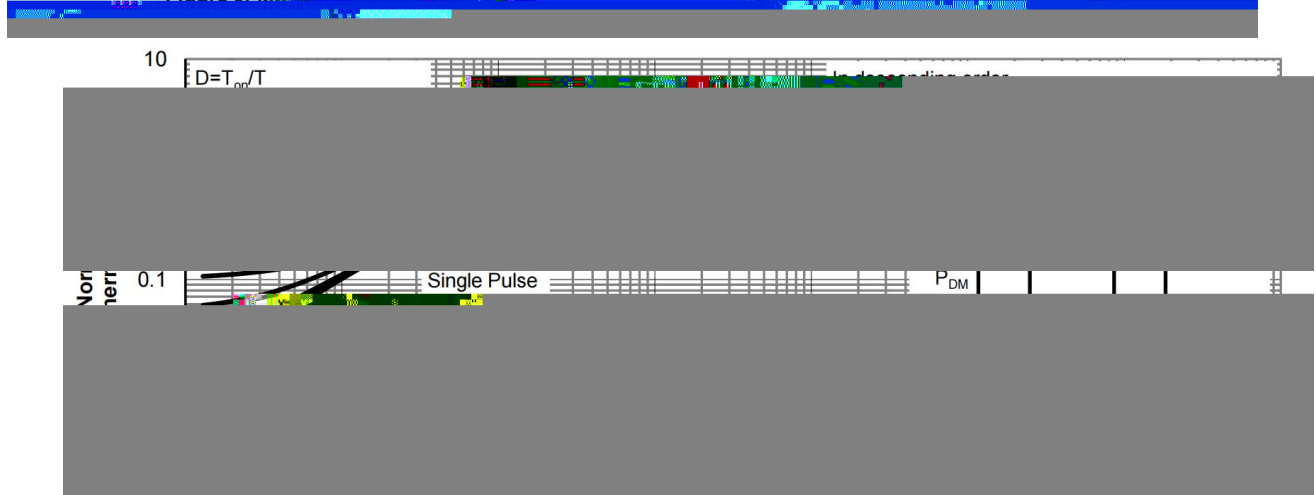
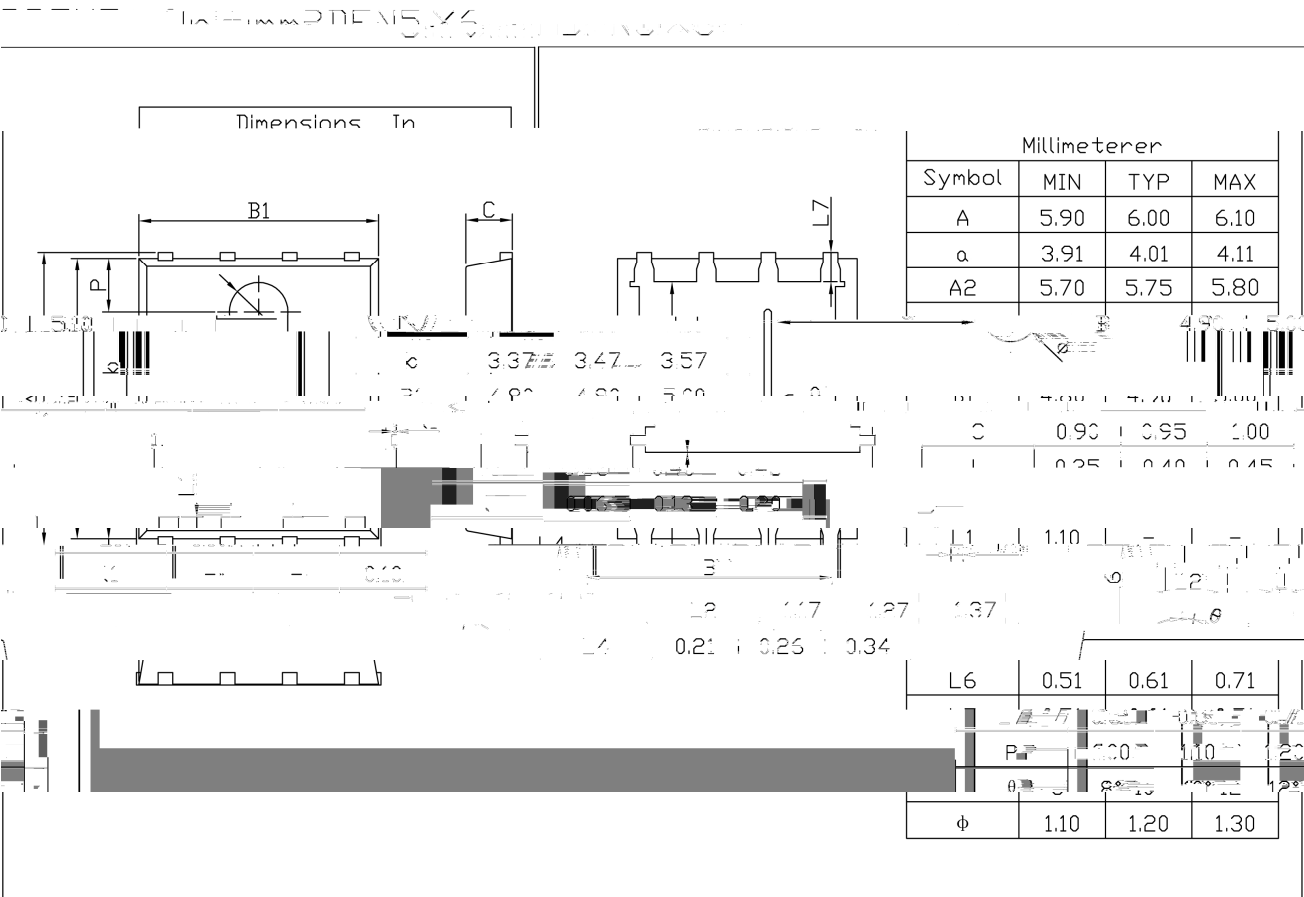
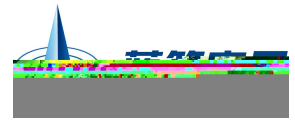


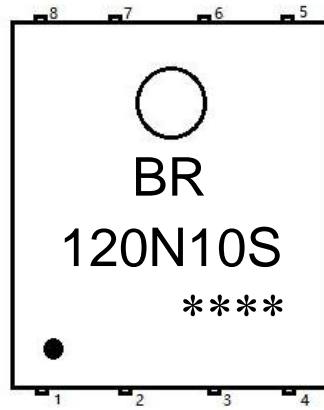
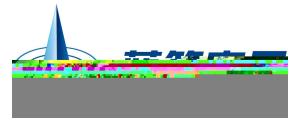
Figure 9: Maximum Forward Bias

Figure 10: Maximum Continuous Drain Current vs Case Temperature





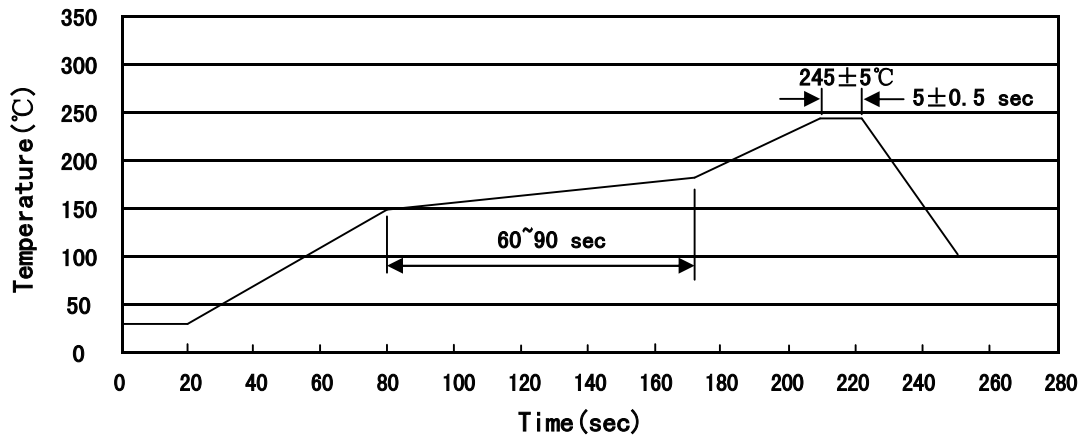
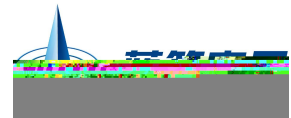
Rev.00 201812



BR  
120N10S

Note

BR	Company Code
120N10S	Product Type.



Note:

- |   |       |     |           |        |  |
|---|-------|-----|-----------|--------|--|
| 1 | 150   | 180 | 60        | 90sec; | 1.Preheating:150~180°C, Time:60~90sec.   |
| 2 | 245±5 |     | 5±0.5sec; |        | 2.Peak Temp.:245±5°C, Duration:5±0.5sec. |
| 3 |       | 2   | 10°C/sec. |        | 3. Cooling Speed: 2~10°C/sec.            |

260±5°C

10±1 sec.

Temp.:260±5°C

Time:10±1 sec

/ REEL

Package Type	Units 包装数量					Dimension 包装尺寸 (unit: mm <sup>3</sup> )		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box	Outer Box
PDFN5*6	5000	2	10000	6	60000	13" × 12	360 × 360 × 50	380 × 335 × 366